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**Silicon NPN Power Transistor****2SC4370****DESCRIPTION**

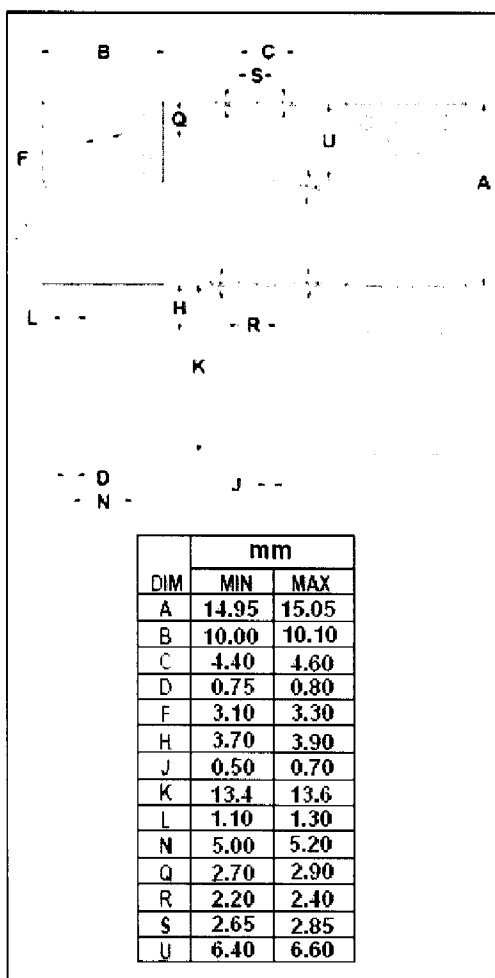
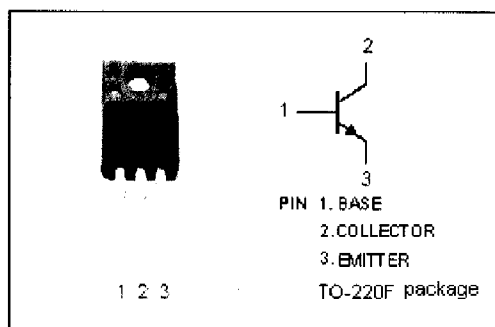
- High Collector-Emitter Breakdown Voltage  
 $V_{CE0} = 160V(\text{Min})$
- Complement to Type 2SA1659
- Full-mold package that does not require an insulating board or bushing when mounting.

**APPLICATIONS**

- Designed for high voltage applications

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	160	V
$V_{CEO}$	Collector-Emitter Voltage	160	V
$V_{EBO}$	Emitter-Base Voltage	5.0	V
$I_{C(DC)}$	Collector Current(DC)	1.5	A
$I_{B(DC)}$	Base Current	0.15	A
$P_C$	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	20	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^\circ\text{C}$



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.



**Quality Semi-Conductors**

**Silicon NPN Power Transistor****2SC4370****ELECTRICAL CHARACTERISTICS****T<sub>j</sub>=25°C unless otherwise specified**

<b>SYMBOL</b>	<b>PARAMETER</b>	<b>CONDITIONS</b>	<b>MIN</b>	<b>TYP.</b>	<b>MAX</b>	<b>UNIT</b>
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10mA; I_B = 0$	160			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 500mA; I_B = 50mA$			1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 500mA; V_{CE} = 5V$			1.0	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = 160V; I_E = 0$			1.0	$\mu A$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = 5V; I_C = 0$			1.0	$\mu A$
$h_{FE}$	DC Current Gain	$I_C = 100mA; V_{CE} = 5V$	70		240	
$C_{OB}$	Output Capacitance	$I_E = 0; V_{CB} = 10V; f = 1.0MHz$		25		pF
$f_T$	Current-Gain—Bandwidth Product	$I_C = 100mA; V_{CE} = 10V$		100		MHz

◆  **$h_{FE}$  Classifications**

<b>O</b>	<b>Y</b>
70-140	120-240